

WHAT IS CLAIMED IS:

Sub ~~10~~ 1

05966313-110004

- A physical quantity detection device comprising: an operational amplifier;
- 5 a first resistor connected between an inverting input of said operational amplifier and a first reference potential;
- a second resistor connected between said inverting input of said operational amplifier and a second reference potential, said first and second resistors having a first temperature coefficient of
- 10 resistance;
- a feedback resistor being connected between said inverting input of said operational amplifier and an output of said operational amplifier and having a second temperature coefficient of resistor; and
- 15 a reference voltage generation circuit generating a reference voltage supplied to a non-inverting input of said operational amplifier, at least one of said first and second resistors comprising a sensing element of which resistance varying on the basis of a physical quantity with a temperature coefficient of sensitivity,
- 20 wherein a difference between said first temperature coefficient of resistance and said temperature coefficient of sensitivity being substantially equal to said second temperature coefficient of resistance.
- 25 2. The physical quantity detection device as claimed in claim 1, wherein each of said first and second resistors and said feedback

resistor comprises a diffused resistor, a concentration of impurity of said feedback resistor is different from concentrations of impurity of said first and second resistors.

5 3. The physical quantity detection device as claimed in claim 2, wherein said concentrations of impurity of said first and second resistors are from $0.4 \times 10^{19} \text{ cm}^{-3}$ to $8 \times 10^{19} \text{ cm}^{-3}$ and said concentration of impurity of said feedback resistor is from $1.6 \times 10^{17} \text{ cm}^{-3}$ to $7 \times 10^{17} \text{ cm}^{-3}$.

10 4. The physical quantity detection device as claimed in claim 1, wherein one of said first and second resistors comprises said sensing element of which resistance varies on the basis of said physical quantity, and a resistance of the other of said first and second resistors remains constant with respect to said physical quantity.

15 5. The physical quantity detection device as claimed in claim 1, wherein said reference voltage generation circuit includes third and fourth resistors connected in series between said first and second reference potentials and generates a divided voltage as said reference voltage, and a temperature coefficient of resistance of said third resistor is substantially equal to a temperature coefficient of resistance of said fourth resistor.

20 6. The physical quantity detection device as claimed in claim 5, wherein one of said third and fourth resistors has a trimming

7. The physical quantity detection device as claimed in claim 1, further comprising a resistor having a trimming structure is connected in parallel with said feedback resistor.

10 a third resistor;

15 a fourth resistor disposed between an output terminal and
inverting input of said another operational amplifier.

10. The physical quantity detection device as claimed in claim 8,
further comprising an offset trimming resistor between said second
25 reference potential and said inverting input of said another
operational amplifier.

fifth and sixth resistors connected between said first reference

seventh and eighth resistors connected between said inverting input of said another operational amplifier and said second reference potential, wherein said sixth and seventh resistors have temperature

12. The physical quantity detection device as claimed in claim 11, wherein at least one of said fifth and eighth resistors has a trimming structure for compensating a temperature characteristic of offset of the output of said another operational amplifier.

13. The physical quantity detection device as claimed in claim 1,
wherein if it is assumed that a sensitivity of said sensing element at a
reference temperature is S_0 , a resistance of said sensing element at
said reference temperature is R_0 , and a resistance of said feedback
resistor at said reference temperature is R_{ts0} , then, it is represented
that said sensitivity of said sensing element at a temperature t which
is different from said reference temperature by T is $S(T)$, said
resistance of said sensing element at t is $R(T)$, and said resistance of
said feedback resistor at t is $R_{ts}(T)$, and $S(T)$, $R(T)$, and $R_{ts}(T)$ are
further represented by:

where said $\alpha_1, \alpha_2, \beta_1, \beta_2, A_1$, and A_2 are temperature coefficients, and wherein said $\alpha_1, \alpha_2, \beta_1, \beta_2, A_1$, and A_2 are determined so as to

5 establish both $A1 = \alpha 1 - \beta 1$ and $A2 = \alpha 2 - \beta 2 - \beta 1 \cdot (\alpha 1 - \beta 1)$.

14. The physical quantity detection device as claimed in claim 1,
wherein said reference voltage is determined such that said almost
all of a current flowing through said first resistor flows into said
10 second resistor.

15. A physical quantity detection device comprising: an operational amplifier;

a first resistor connected between an inverting input of said
15 operational amplifier and a first reference potential;

a second resistor connected between said inverting input of said operational amplifier and a second reference potential, said first and second resistors having a first temperature coefficient of resistance;

20 a feedback resistor being connected between said inverting
input of said operational amplifier and an output of said operational
amplifier and having a second temperature coefficient of resistor;
and

25 a reference voltage generation circuit generating a reference voltage supplied to a non-inverting input of said operational amplifier, at least one of said first and second resistors comprising a

0536613-1000-7
Lab Cont

sensing element of which resistance varying on the basis of a physical quantity with a temperature coefficient of sensitivity, wherein said reference voltage generation circuit includes a third and fourth resistors connected in series between said first and
5 second reference potentials and generates a divided voltage as said reference voltage, and a temperature coefficient of said third resistor is substantially equal to a temperature coefficient of said fourth resistor.

0958667405004
Ad6
Cont

- 10 16. A physical quantity detection device comprising:
an operational amplifier;
a first resistor connected between an inverting input of said operational amplifier and a first reference potential;
a second resistor connected between said inverting input of
15 said operational amplifier and a second reference potential, said first and second resistors having a first temperature coefficient of resistance;
a feedback resistor being connected between said inverting input of said operational amplifier and an output of said operational
20 amplifier and having a second temperature coefficient of resistor;
a reference voltage generation circuit generating a reference voltage supplied to a non-inverting input of said operational amplifier, at least one of said first and second resistors comprising a sensing element of which resistance varying on the basis of a
25 physical quantity with a temperature coefficient of sensitivity,
a third resistor;

another operational amplifier, an inverting input of said
another operational amplifier being supplied with an output of said
operational amplifier through said third resistor, a non-inverting
input of said another operational amplifier being supplied with said
5 reference voltage; and

a fourth resistor disposed between an output terminal and
inverting input of said another operational amplifier.

17. The physical quantity detection device as claimed in claim 3,
10 wherein said concentrations of impurity of said first and second
resistors are from $0.8 \times 10^{19} \text{ cm}^{-3}$ to $4 \times 10^{19} \text{ cm}^{-3}$ and said
concentration of impurity of said feedback resistor is from 2.5×10^{17}
 cm^{-3} to $5.5 \times 10^{17} \text{ cm}^{-3}$.

18. The physical quantity detection device as claimed in claim 17,
15 wherein said concentrations of impurity of said first and second
resistors are about $1 \times 10^{19} \text{ cm}^{-3}$, and said concentration of impurity of
said feedback resistor is about $4 \times 10^{17} \text{ cm}^{-3}$.